

ABSTRACT OF THE DISCLOSURE

A semiconductor device having: a semiconductor substrate with an isolation region defining a plurality of active regions; a gate electrode formed above each active region, constituting a semiconductor element; an interlevel insulator covering the gate electrode; local interconnects formed through the interlevel insulator and electrically connected to the semiconductor element; local interconnect dummies formed through the interlevel insulator and electrically separated from the local interconnects; and lower level dummies, each comprising either one of an active region dummy, a laminated dummy of an active region dummy and a gate electrode dummy formed thereon, and a gate electrode dummy formed on the isolation region, wherein each of the local interconnect dummies is not connected to two or more lower level dummies.